

## FEATURES

- IGBT<sup>3</sup> CHIP(1700V Trench+Field Stop technology)
- Low turn-off losses, short tail current
- $V_{CE(sat)}$  with positive temperature coefficient
- DIODE CHIP(1700V EMCON 3 technology)
- Free wheeling diodes with fast and soft reverse recovery



## APPLICATIONS

- High frequency switching application
- Medical applications
- Motion/servo control
- UPS systems

## ABSOLUTE MAXIMUM RATINGS

$T_C=25^{\circ}\text{C}$  unless otherwise specified

Symbol	Parameter	Test Conditions	Values	Unit
<b>IGBT</b>				
$V_{CES}$	Collector - Emitter Voltage	$T_{vj}=25^{\circ}\text{C}$	1700	V
$V_{GES}$	Gate - Emitter Voltage		$\pm 20$	V
$I_c$	DC Collector Current	$T_C=25^{\circ}\text{C}$	250	A
		$T_C=80^{\circ}\text{C}$	150	A
$I_{CM}$	Repetitive Peak Collector Current	$t_p=1\text{ms}$	300	A
$P_{tot}$	Power Dissipation Per IGBT		890	W
<b>Diode</b>				
$V_{RRM}$	Repetitive Reverse Voltage	$T_{vj}=25^{\circ}\text{C}$	1700	V
$I_{F(AV)}$	Average Forward Current	$T_C=25^{\circ}\text{C}$	250	A
		$T_C=80^{\circ}\text{C}$	150	A
$I_{FRM}$	Repetitive Peak Forward Current	$t_p=1\text{ms}$	300	A
$I^2t$		$T_{vj}=125^{\circ}\text{C}, t=10\text{ms}, V_R=0\text{V}$	4200	$\text{A}^2\text{s}$

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### ELECTRICAL AND THERMAL CHARACTERISTICS $T_C=25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
<b>IGBT</b>						
$V_{GE(th)}$	Gate - Emitter Threshold Voltage	$V_{CE}=V_{GE}, I_C=6.0\text{mA}$	5.2	5.8	6.4	V
$V_{CE(sat)}$	Collector - Emitter Saturation Voltage	$I_C=150\text{A}, V_{GE}=15\text{V}, T_{Vj}=25^\circ\text{C}$		2.0	2.45	V
		$I_C=150\text{A}, V_{GE}=15\text{V}, T_{Vj}=125^\circ\text{C}$		2.4		V
$I_{CES}$	Collector Leakage Current	$V_{CE}=1700\text{V}, V_{GE}=0\text{V}, T_{Vj}=25^\circ\text{C}$			3	mA
		$V_{CE}=1700\text{V}, V_{GE}=0\text{V}, T_{Vj}=125^\circ\text{C}$			20	mA
$I_{GES}$	Gate Leakage Current	$V_{CE}=0\text{V}, V_{GE} \pm 20\text{V}, T_{Vj}=125^\circ\text{C}$	-400		400	nA
$R_{gint}$	Integrated Gate Resistor			4.3		$\Omega$
$Q_{ge}$	Gate Charge	$V_{CE}=900\text{V}, I_C=150\text{A}, V_{GE}=\pm 15\text{V}$		1.8		$\mu\text{C}$
$C_{ies}$	Input Capacitance	$V_{CE}=25\text{V}, V_{GE}=0\text{V}, f=1\text{MHz}$		13.6		nF
$C_{res}$	Reverse Transfer Capacitance			0.45		nF
$t_{d(on)}$	Turn - on Delay Time	$V_{CC}=900\text{V}, I_C=150\text{A}, T_{Vj}=25^\circ\text{C}$		380		ns
		$R_G=3.3\Omega, T_{Vj}=125^\circ\text{C}$		420		ns
$t_r$	Rise Time	$V_{GE}=\pm 15\text{V}, T_{Vj}=25^\circ\text{C}$		50		ns
		Inductive Load $T_{Vj}=125^\circ\text{C}$		60		ns
$t_{d(off)}$	Turn - off Delay Time	$V_{CC}=900\text{V}, I_C=150\text{A}, T_{Vj}=25^\circ\text{C}$		700		ns
		$R_G=3.3\Omega, T_{Vj}=125^\circ\text{C}$		900		ns
$t_f$	Fall Time	$V_{GE}=\pm 15\text{V}, T_{Vj}=25^\circ\text{C}$		180		ns
		Inductive Load $T_{Vj}=125^\circ\text{C}$		300		ns
$E_{on}$	Turn - on Energy	$V_{CC}=900\text{V}, I_C=150\text{A}, T_{Vj}=25^\circ\text{C}$		33		mJ
		$R_G=3.3\Omega, T_{Vj}=125^\circ\text{C}$		48		mJ
$E_{off}$	Turn - off Energy	$V_{GE}=\pm 15\text{V}, T_{Vj}=25^\circ\text{C}$		32		mJ
		Inductive Load $T_{Vj}=125^\circ\text{C}$		47		mJ
$I_{sc}$	Short Circuit Current	$t_{psc} \leq 10\mu\text{s}, V_{GE}=15\text{V}$ $T_{Vj}=125^\circ\text{C}, V_{CC}=1000\text{V}$		600		A
$R_{thJC}$	Junction-to-Case Thermal Resistance ( Per IGBT )				0.14	K/W
<b>Diode</b>						
$V_F$	Forward Voltage	$I_F=150\text{A}, V_{GE}=0\text{V}, T_{Vj}=25^\circ\text{C}$		1.8	2.2	V
		$I_F=150\text{A}, V_{GE}=0\text{V}, T_{Vj}=125^\circ\text{C}$		1.9		V
$I_{RRM}$	Max. Reverse Recovery Current	$I_F=150\text{A}, V_R=900\text{V}$		240		A
$Q_{rr}$	Reverse Recovery Charge	$di_F/dt=-3600\text{A}/\mu\text{s}$		72		$\mu\text{C}$
$E_{rec}$	Reverse Recovery Energy	$T_{Vj}=125^\circ\text{C}$		41		mJ
$R_{thJCD}$	Junction-to-Case Thermal Resistance ( Per Diode )				0.21	K/W

**MODULE CHARACTERISTICS**

*T<sub>C</sub>=25°C unless otherwise specified*

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
T <sub>Vj max</sub>	Max. Junction Temperature				175	°C
T <sub>Vj op</sub>	Operating Temperature		-40		150	°C
T <sub>stg</sub>	Storage Temperature		-40		150	°C
V <sub>isol</sub>	Insulation Test Voltage	AC, t=1min		4000		V
CTI	Comparative Tracking Index		350			
Torque	Module-to-Sink	Recommended (M6)	3		5	N · m
Torque	Module Electrodes	Recommended (M6)	2.5		5	N · m
Weight				320		g

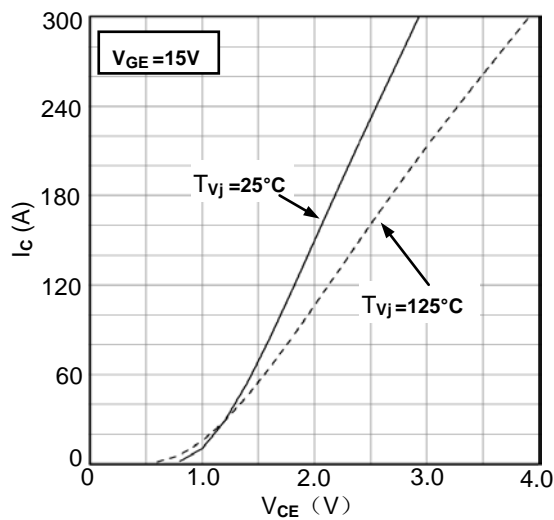


Figure1. Typical Output Characteristics

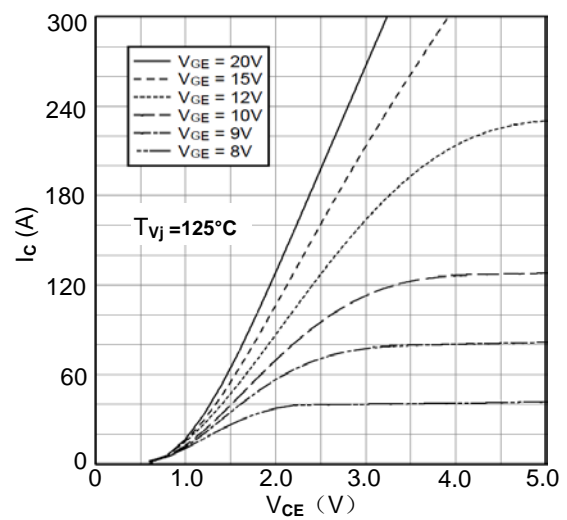


Figure2. Typical Output Characteristics

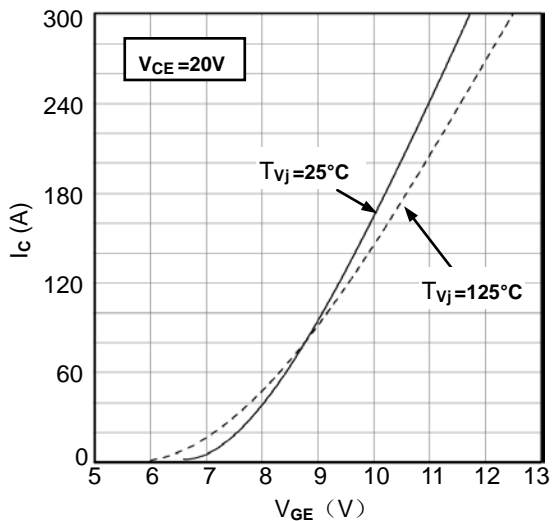


Figure3. Typical Transfer characteristics

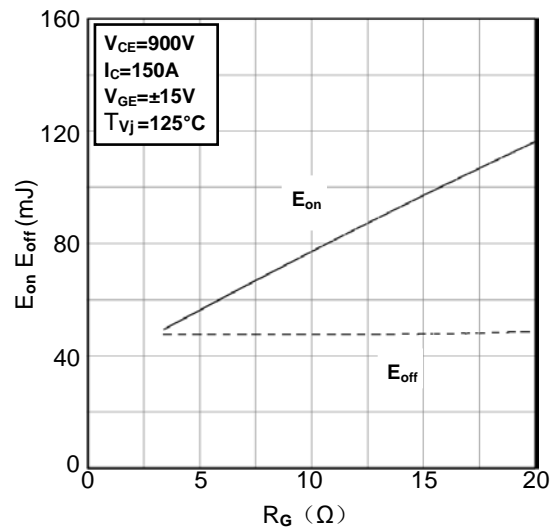


Figure4. Switching Energy vs. Gate Resistor

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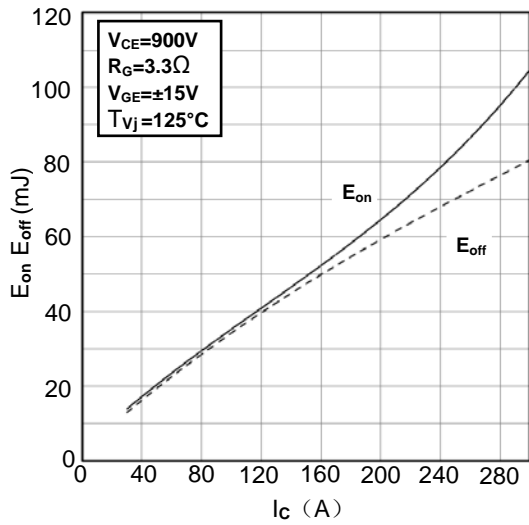


Figure 5. Switching Energy vs. Collector Current

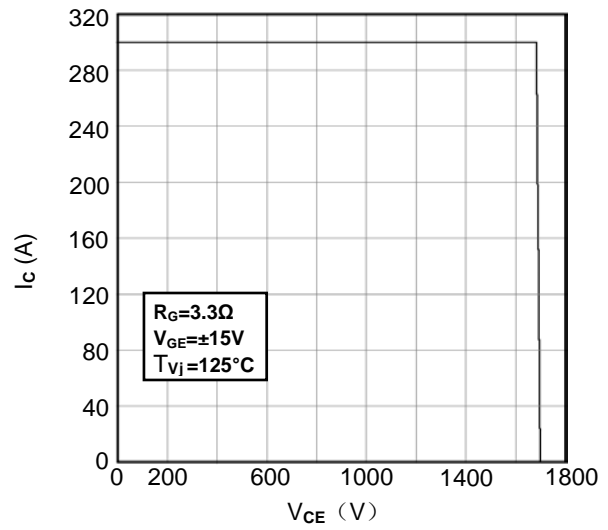


Figure 6. Reverse Biased Safe Operating Area

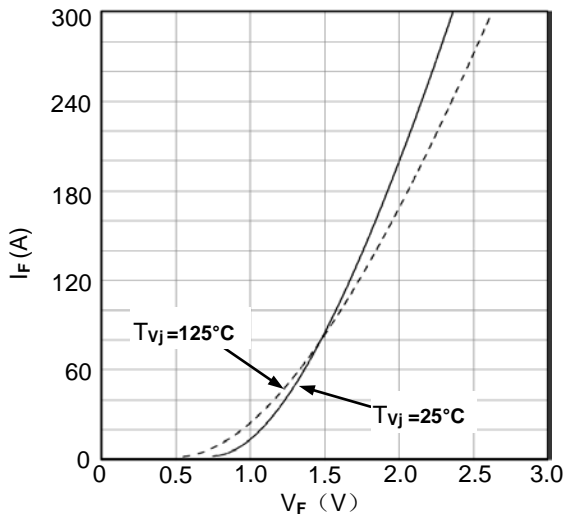


Figure 7. Diode Forward Characteristics

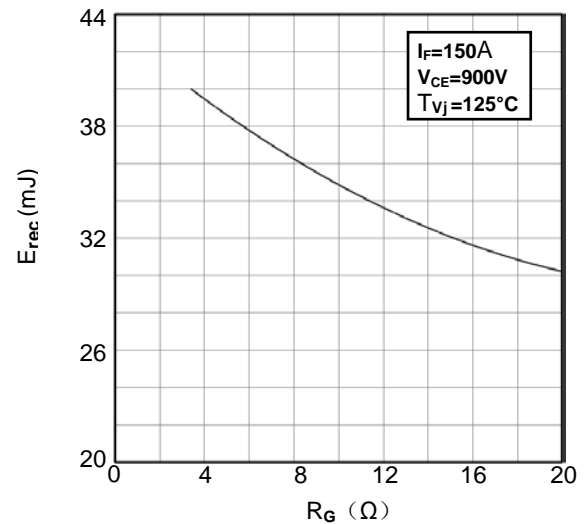


Figure 8. Switching Energy vs. Gate Resistor

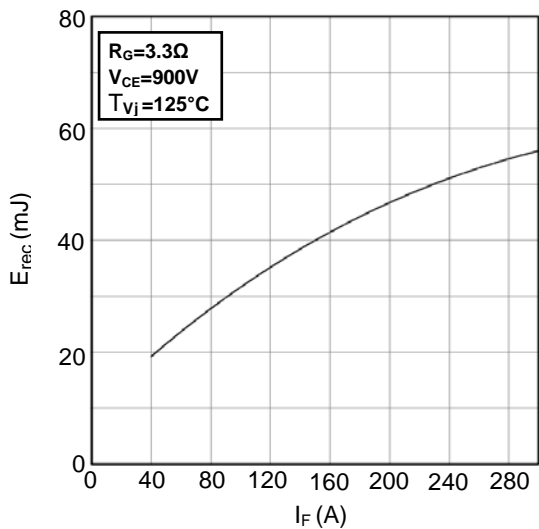


Figure 9. Switching Energy vs. Forward Current

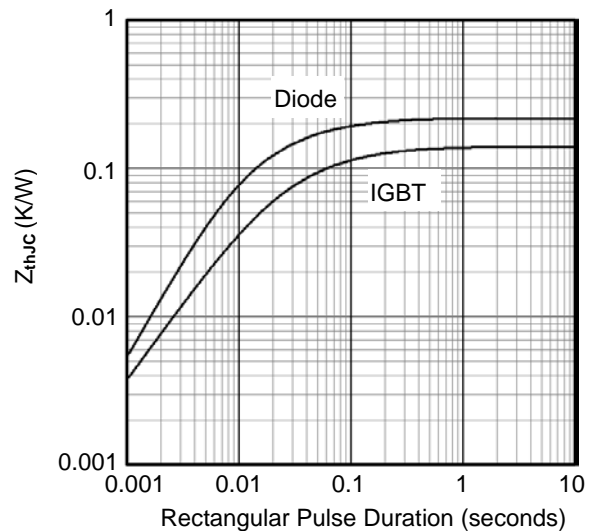


Figure 10. Transient Thermal Impedance of Diode and IGBT

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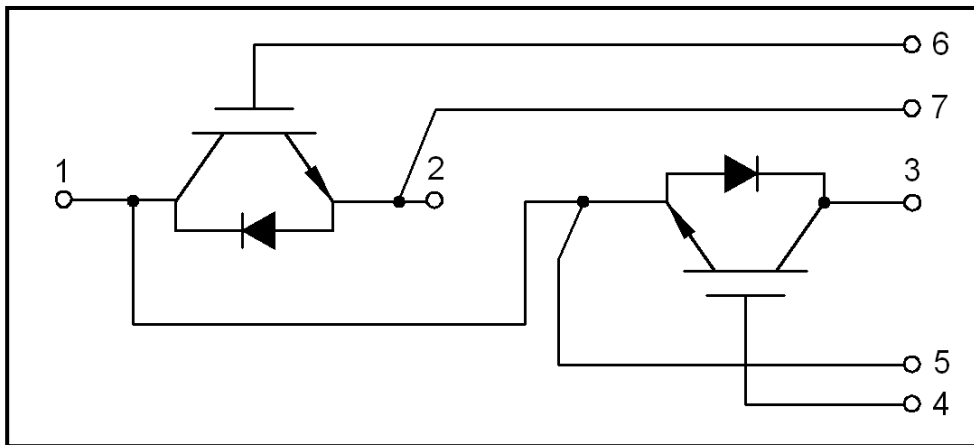
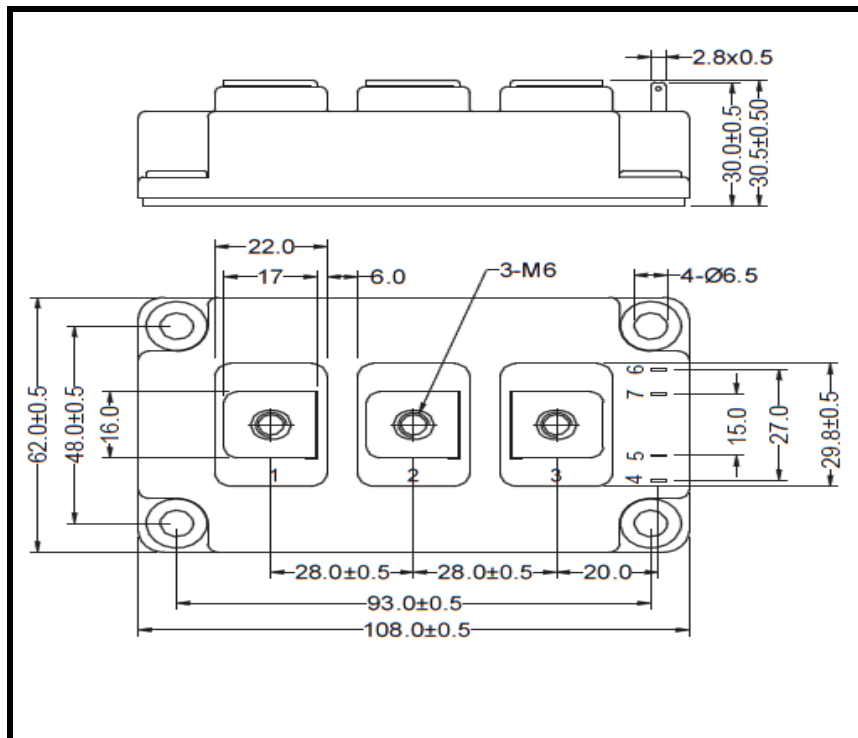


Figure11. Circuit Diagram



Dimensions (mm)  
Figure12. Package Outline